RoHS
Available on commercial versions

Voidless Hermetically Sealed Unidirectional Transient Voltage Suppressors

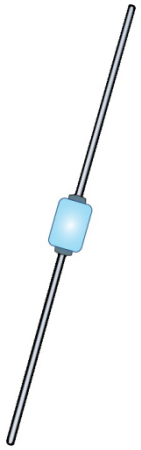
Qualified per MIL-PRF-19500/551

Qualified Levels:
JAN, JANTX, and JANTXV

DESCRIPTION

This series of 500 watt voidless hermetically sealed unidirectional Transient Voltage Suppressors (TVS) are military qualified to MIL-PRF-19500/551 and are ideal for high-reliability applications where a failure cannot be tolerated. Working peak "standoff" voltages are available from 5.0 to 51.6 volts. They are very robust, using a hard glass casing and internal Category 1 metallurgical bonds. These devices are also available in a surface mount MELF package configuration.

Important: For the latest information, visit our website http://www.microsemi.com.



"B" Package

Also available in:

"B" SQ-MELF Package
(surface mount)
1N6461US - 1N6468US

FEATURES

- Popular JEDEC registered 1N6461 thru 1N6468 series.
- Available as 500 W peak pulse power (P_{PP}).
- Working peak "standoff" voltage (V_{WM}) from 5.0 to 51.6 V.
- High surge current and peak pulse power provides transient voltage protection for sensitive circuits.
- Triple-layer passivation.
- Internal "*Category 1*" metallurgical bonds.
- Voidless hermetically sealed glass package.
- JAN, JANTX, and JANTXV qualifications available per MIL-PRF-19500/551. Other screening in reference to MIL-PRF-19500 is also available.
  (See part nomenclature for all available options.)
- RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- Military and other high-reliability transient protection.
- Extremely robust construction.
- ESD and EFT protection per IEC61000-4-2 and IEC61000-4-4 respectively.
- Protection from secondary effects of lightning per select levels in IEC61000-4-5.
- Flexible axial-leaded mounting terminals.
- Nonsensitive to ESD per MIL-STD-750 method 1020.
- Inherently radiation hard as described in Microsemi "MicroNote 050".

MAXIMUM RATINGS @ 25 ºC

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-55 to +175	^oC
Thermal Resistance, Junction to Lead (1)	$R_{\Theta JL}$	60	ºC/W
Forward Surge Current @ 8.3 ms half-sine	I_{FSM}	80	A
Forward Voltage @ 1 Amp	V_F	1.5	V
Peak Pulse Power @ 10/1000 µs	P_{PP}	500	W
Reverse Power Dissipation (2)	P_R	2.5	W
Solder Temperature @ 10 s		260	^oC

Notes: 1. At L = 0.375 inch (9.53 mm) from body.
2. Derate at 16.7 mW/^{o}C (see figure 4).

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MECHANICAL and PACKAGING

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Axial-leads are tin/lead over copper. RoHS compliant matte-tin is available for commercial grade only.
- MARKING: Body paint and part number.
- POLARITY: Cathode band.
- TAPE & REEL option: Standard per EIA-296. Contact factory for quantities.
- WEIGHT: Approximately 750 milligrams.
- See Package Dimensions on last page.

PART NOMENCLATURE

JAN **1N6461** **e3**

Reliability Level
JAN = JAN Level
JANTX = JANTX Level
JANTXV = JANTXV Level
CDS (reference JANS)
Blank = commercial

JEDEC type number
See Electrical Characteristics table

RoHS Compliance
e3 = RoHS compliant (available on commercial grade only)
Blank = non-RoHS compliant

SYMBOLS & DEFINITIONS

Symbol	Definition
$\alpha_{V(BR)}$	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by the change in temperature expressed in %/°C or mV/°C.
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current $I_{(BR)}$ in the breakdown region.
V_{WM}	Rated working standoff voltage: The maximum-rated value of dc or repetitive peak positive cathode-to-anode voltage that may be continuously applied over the standard operating temperature.
I_D	Standby Current: The current through the device at rated stand-off voltage.
I_{PP}	Peak Impulse Current: The maximum rated random recurring peak impulse current or nonrepetitive peak impulse current that may be applied to a device. A random recurring or nonrepetitive transient current is usually due to an external cause, and it is assumed that its effect will have completely disappeared before the next transient arrives.
V_C	Clamping Voltage: The voltage across the device in a region of low differential resistance during the application of an impulse current (I_{PP}) for a specified waveform.
P_{PP}	Peak Pulse Power. The rated random recurring peak impulse power or rated nonrepetitive peak impulse power. The impulse power is the maximum-rated value of the product of I_{PP} and V_C.

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ELECTRICAL CHARACTERISTICS

TYPE	MINIMUM BREAK DOWN VOLTAGE $V_{(BR)}$ @ $I_{(BR)}$	BREAKDOWN CURRENT $I_{(BR)}$	RATED WORKING STANDOFF VOLTAGE V_{WM}	MAXIMUM STANDBY CURRENT I_D @ V_{WM}	MAXIMUM CLAMPING VOLTAGE V_C @ 10/1000 µs	MAXIMUM PEAK IMPULSE CURRENT I_{PP}		MAXIMUM TEMP. COEF. OF $\alpha_{V(BR)}$
						@ 8/20 µs	@ 10/1000 µs	
	Volts	mA	V (pk)	µA	V (pk)	A (pk)	A (pk)	%/°C
1N6461	5.6	25	5	3000	9.0	315	56	-0.03, +0.045
1N6462	6.5	20	6	2500	11.0	258	46	+0.060
1N6463	13.6	5	12	500	22.6	125	22	+0.085
1N6464	16.4	5	15	500	26.5	107	19	+0.085
1N6465	27.0	2	24	50	41.4	69	12	+0.096
1N6466	33.0	1	30.5	3	47.5	63	11	+0.098
1N6467	43.7	1	40.3	2	63.5	45	8	+0.101
1N6468	54.0	1	51.6	2	78.5	35	6	+0.103

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GRAPHS

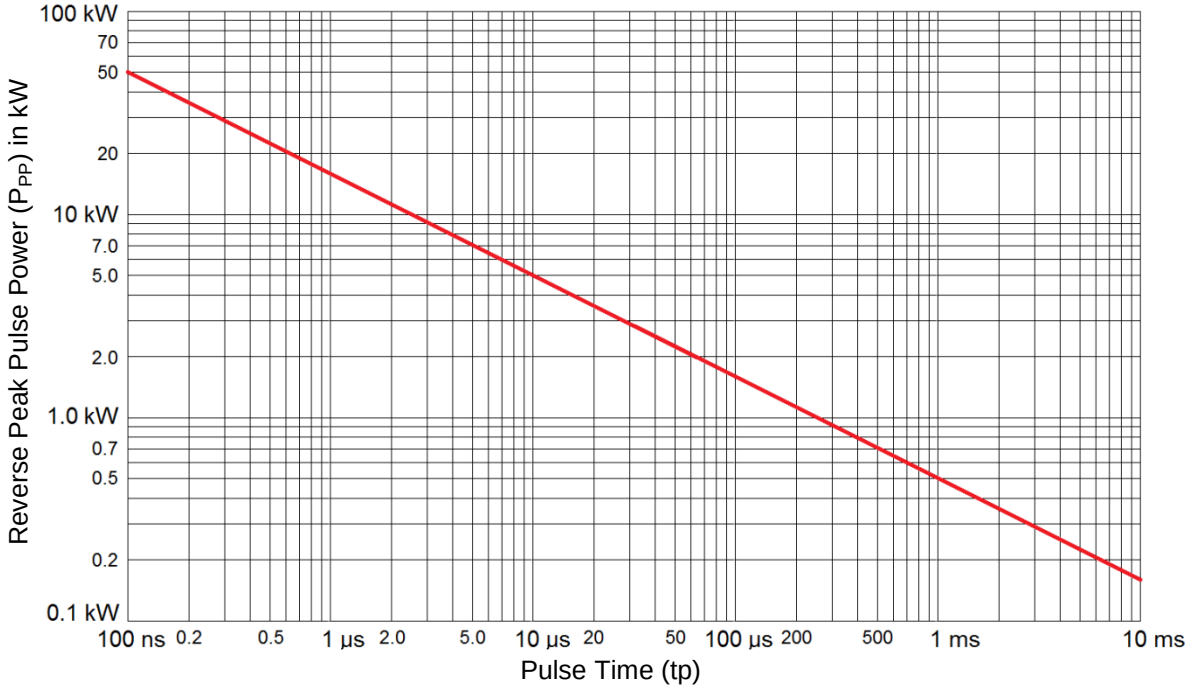

FIGURE 1
Peak Pulse Power vs Pulse Time

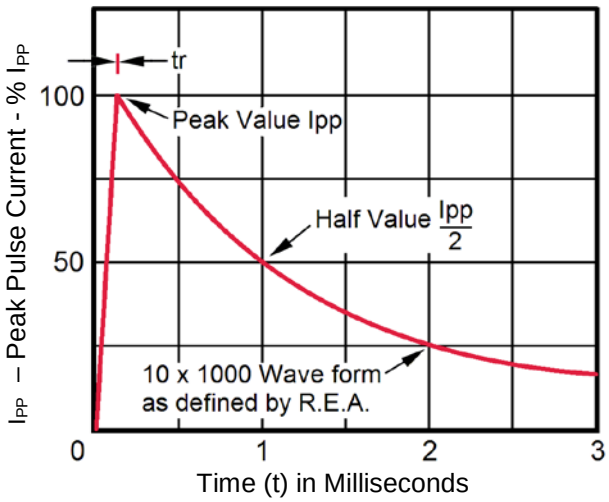

FIGURE 2
10/1000 µs Current Impulse Waveform

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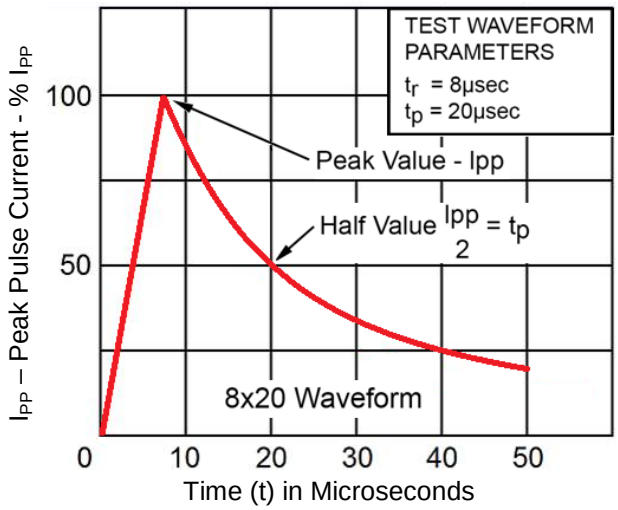

FIGURE 3
8/20 µs Current Impulse Waveform

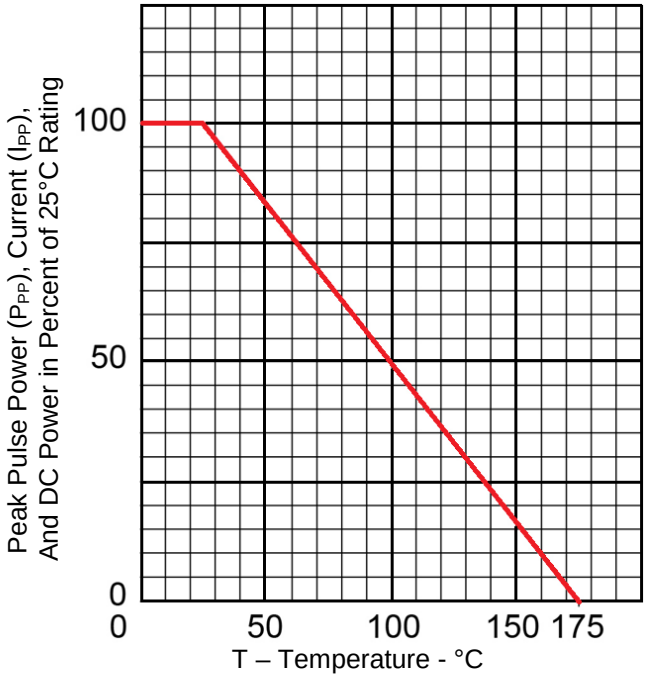

FIGURE 4
Derating Curve

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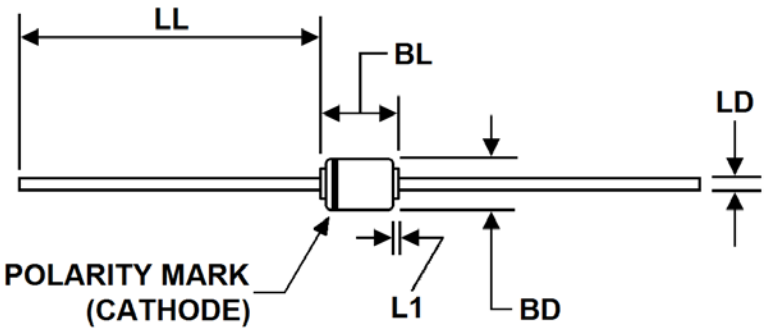
PACKAGE DIMENSIONS



Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
BD	0.115	0.145	2.92	3.68	3,4
BL	0.150	0.300	3.81	7.62	4
LD	0.037	0.042	0.94	1.07	4
LL	0.900	1.30	22.86	33.02	
L1		0.050		1.27	4

NOTES:

1. Dimensions are in inches.
2. Millimeter equivalents are given for information only.
3. Dimension BD shall be measured at the largest diameter.
4. Dimension BL includes dimension L1 region in which the diameter may vary from BD maximum to LD minimum.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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